

## General Description

The GreenMOS<sup>®</sup> high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS<sup>®</sup> Z series is integrated with fast recovery diode (FRD) to minimize reverse recovery time. It is suitable for resonant switching topologies to reach higher efficiency, higher reliability and smaller form factor.

## Features

- Low  $R_{DS(ON)}$  & FOM
- Extremely low switching loss
- Excellent stability and uniformity

GreenMOS<sup>®</sup>



## Applications

- LED lighting
- Telecom
- Adapter
- Sever
- Solar/UPS

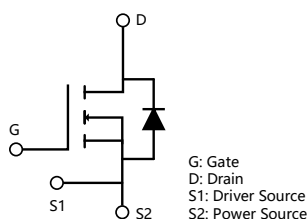
## Key Performance Parameters

| Parameter                         | Value | Unit       |
|-----------------------------------|-------|------------|
| $V_{DS}$                          | 650   | V          |
| $I_D$ , pulse                     | 58    | A          |
| $R_{DS(ON)}$ , max @ $V_{GS}=10V$ | 130   | m $\Omega$ |
| $Q_g$                             | 45    | nC         |
| PD                                | 178   | W          |

## Marking Information

| Product Name     | Package | Marking       |
|------------------|---------|---------------|
| OSG65R130JT3ZF-F | PDFN8*8 | OSG65R130JT3Z |

## Package & Pin Information



**Absolute Maximum Ratings** at  $T_j=25^{\circ}\text{C}$  unless otherwise noted

| Parameter                                                                 | Symbol         | Value      | Unit               |
|---------------------------------------------------------------------------|----------------|------------|--------------------|
| Drain-source voltage                                                      | $V_{DS}$       | 650        | V                  |
| Gate-source voltage (static)                                              | $V_{GS}$       | $\pm 20$   | V                  |
| Gate-source voltage (dynamic)                                             | $V_{GS,pulse}$ | $\pm 30$   | V                  |
| Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$         | $I_D$          | 25         | A                  |
| Continuous drain current <sup>1)</sup> , $T_C=100^{\circ}\text{C}$        |                | 15.8       |                    |
| Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$             | $I_{D,pulse}$  | 75         | A                  |
| Continuous diode forward current <sup>1)</sup> , $T_C=25^{\circ}\text{C}$ | $I_S$          | 25         | A                  |
| Diode pulsed current <sup>2)</sup> , $T_C=25^{\circ}\text{C}$             | $I_{S,pulse}$  | 75         | A                  |
| Power dissipation <sup>3)</sup> , $T_C=25^{\circ}\text{C}$                | $P_D$          | 178        | W                  |
| Single pulsed avalanche energy <sup>5)</sup>                              | $E_{AS}$       | 360        | mJ                 |
| MOSFET dv/dt ruggedness, $V_{DS}=0\ldots 400\text{ V}$                    | dv/dt          | 100        | V/ns               |
| Reverse diode dv/dt, $V_{DS}=0\ldots 400\text{ V}$ , $I_{SD}\leq I_D$     | dv/dt          | 50         | V/ns               |
| Operation and storage temperature                                         | $T_{stg}, T_j$ | -55 to 150 | $^{\circ}\text{C}$ |

**Thermal Characteristics**

| Parameter                                          | Symbol          | Value | Unit                 |
|----------------------------------------------------|-----------------|-------|----------------------|
| Thermal resistance, junction-case                  | $R_{\theta JC}$ | 0.7   | $^{\circ}\text{C/W}$ |
| Thermal resistance, junction-ambient <sup>4)</sup> | $R_{\theta JA}$ | 62    | $^{\circ}\text{C/W}$ |

**Electrical Characteristics** at  $T_j=25^{\circ}\text{C}$  unless otherwise specified

| Parameter                        | Symbol       | Min. | Typ. | Max. | Unit          | Test condition                                                         |
|----------------------------------|--------------|------|------|------|---------------|------------------------------------------------------------------------|
| Drain-source breakdown voltage   | $BV_{DSS}$   | 650  |      |      | V             | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$                                |
| Gate threshold voltage           | $V_{GS(th)}$ | 3.5  |      | 5.5  | V             | $V_{DS}=V_{GS}$ , $I_D=1\text{ mA}$                                    |
| Drain-source on-state resistance | $R_{DS(ON)}$ |      | 99   | 130  | m $\Omega$    | $V_{GS}=10\text{ V}$ , $I_D=12.5\text{ A}$                             |
|                                  |              |      | 248  |      |               | $V_{GS}=10\text{ V}$ , $I_D=12.5\text{ A}$ , $T_j=150^{\circ}\text{C}$ |
| Gate-source leakage current      | $I_{GSS}$    |      |      | 100  | nA            | $V_{GS}=20\text{ V}$                                                   |
|                                  |              |      |      | -100 |               | $V_{GS}=-20\text{ V}$                                                  |
| Drain-source leakage current     | $I_{DSS}$    |      |      | 10   | $\mu\text{A}$ | $V_{DS}=650\text{ V}$ , $V_{GS}=0\text{ V}$                            |
| Gate resistance                  | $R_G$        |      | 14.6 |      | $\Omega$      | $f=1\text{ MHz}$ , Open drain                                          |

### Dynamic Characteristics

| Parameter                                    | Symbol       | Min. | Typ. | Max. | Unit | Test condition                                                                              |
|----------------------------------------------|--------------|------|------|------|------|---------------------------------------------------------------------------------------------|
| Input capacitance                            | $C_{iss}$    |      | 2206 |      | pF   | $V_{GS}=0\text{ V}$ ,<br>$V_{DS}=50\text{ V}$ ,<br>$f=100\text{ kHz}$                       |
| Output capacitance                           | $C_{oss}$    |      | 113  |      | pF   |                                                                                             |
| Reverse transfer capacitance                 | $C_{rss}$    |      | 3.2  |      | pF   |                                                                                             |
| Effective output capacitance, energy related | $C_{o(er)}$  |      | 74   |      | pF   | $V_{GS}=0\text{ V}$ ,<br>$V_{DS}=0\text{ V}-400\text{ V}$                                   |
| Effective output capacitance, time related   | $C_{o(tr)}$  |      | 424  |      | pF   |                                                                                             |
| Turn-on delay time                           | $t_{d(on)}$  |      | 33   |      | ns   | $V_{GS}=10\text{ V}$ ,<br>$V_{DS}=400\text{ V}$ ,<br>$R_G=2\ \Omega$ ,<br>$I_D=20\text{ A}$ |
| Rise time                                    | $t_r$        |      | 73   |      | ns   |                                                                                             |
| Turn-off delay time                          | $t_{d(off)}$ |      | 71   |      | ns   |                                                                                             |
| Fall time                                    | $t_f$        |      | 24   |      | ns   |                                                                                             |

### Gate Charge Characteristics

| Parameter            | Symbol        | Min. | Typ. | Max. | Unit | Test condition                                                         |
|----------------------|---------------|------|------|------|------|------------------------------------------------------------------------|
| Total gate charge    | $Q_g$         |      | 45   |      | nC   | $V_{GS}=10\text{ V}$ ,<br>$V_{DS}=400\text{ V}$ ,<br>$I_D=20\text{ A}$ |
| Gate-source charge   | $Q_{gs}$      |      | 15   |      | nC   |                                                                        |
| Gate-drain charge    | $Q_{gd}$      |      | 16   |      | nC   |                                                                        |
| Gate plateau voltage | $V_{plateau}$ |      | 7.5  |      | V    |                                                                        |

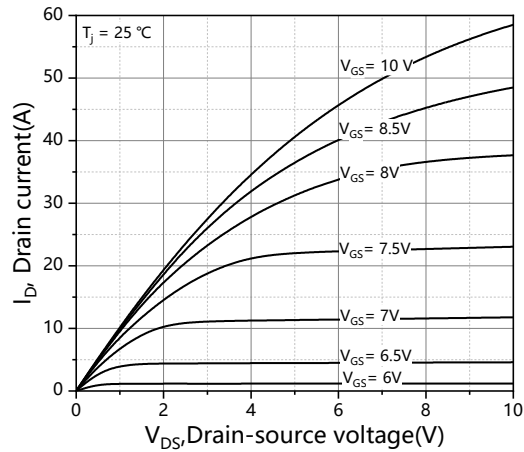
### Body Diode Characteristics

| Parameter                     | Symbol    | Min. | Typ. | Max. | Unit          | Test condition                                                                  |
|-------------------------------|-----------|------|------|------|---------------|---------------------------------------------------------------------------------|
| Diode forward voltage         | $V_{SD}$  |      |      | 1.3  | V             | $I_S=25\text{ A}$ ,<br>$V_{GS}=0\text{ V}$                                      |
| Reverse recovery time         | $t_{rr}$  |      | 148  |      | ns            | $V_R=400\text{ V}$ ,<br>$I_S=20\text{ A}$ ,<br>$di/dt=100\text{ A}/\mu\text{s}$ |
| Reverse recovery charge       | $Q_{rr}$  |      | 0.9  |      | $\mu\text{C}$ |                                                                                 |
| Peak reverse recovery current | $I_{rrm}$ |      | 12.1 |      | A             |                                                                                 |

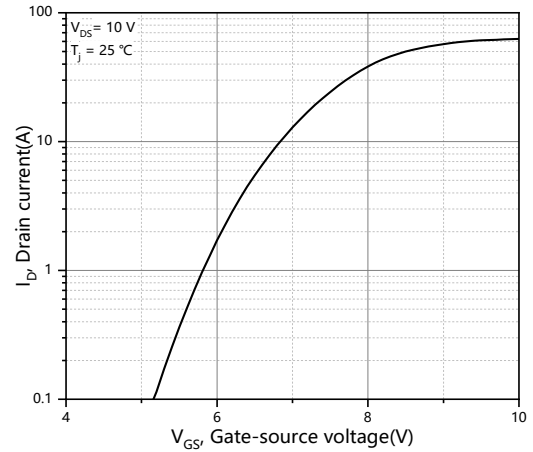
### Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 inch<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^{\circ}\text{C}$ .
- 5)  $V_{DD}=100\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $L=80\text{ mH}$ , starting  $T_j=25\text{ }^{\circ}\text{C}$ .

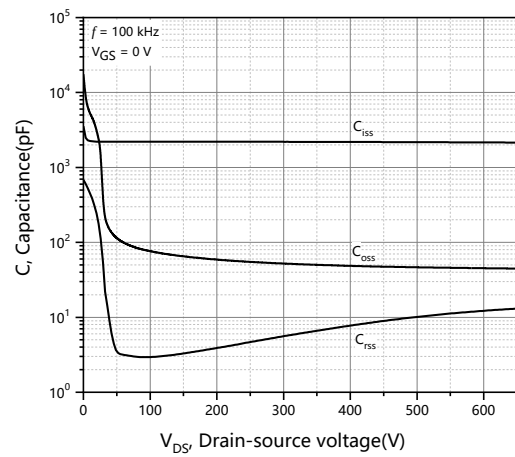
## Electrical Characteristics Diagrams



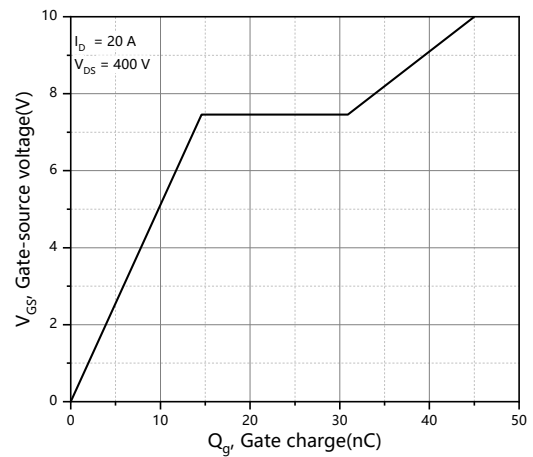
**Figure 1. Typ. output characteristics  $T_j=25^{\circ}\text{C}$**



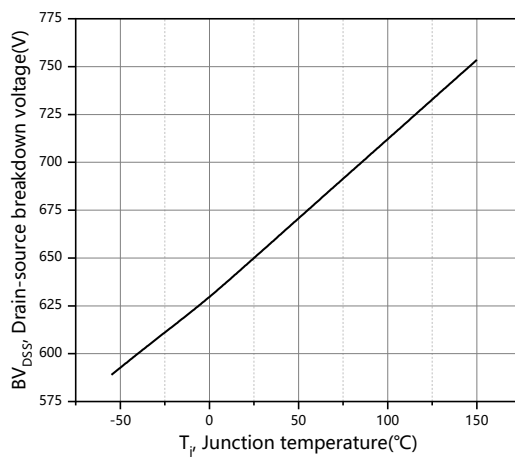
**Figure 2. Typ. transfer characteristics**



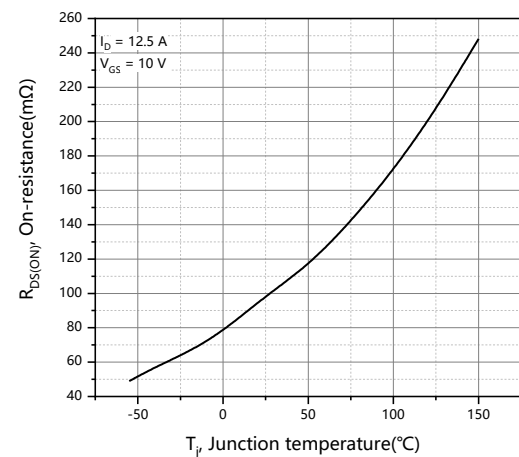
**Figure 3. Typ. capacitances**



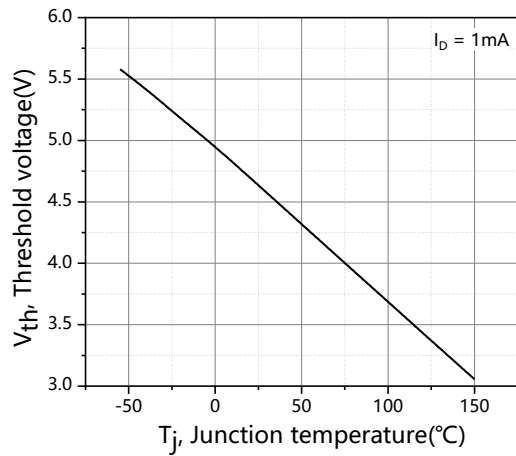
**Figure 4. Typ. gate charge**



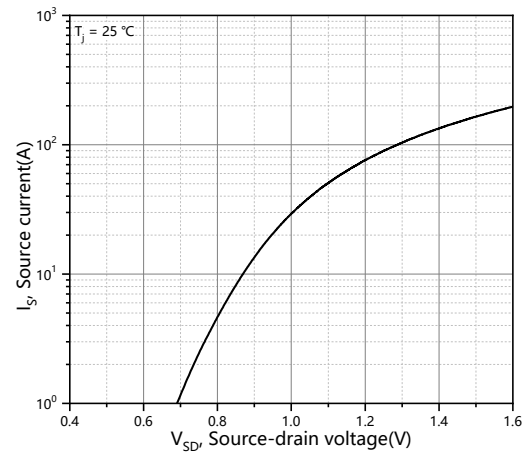
**Figure 5. Drain-source breakdown voltage**



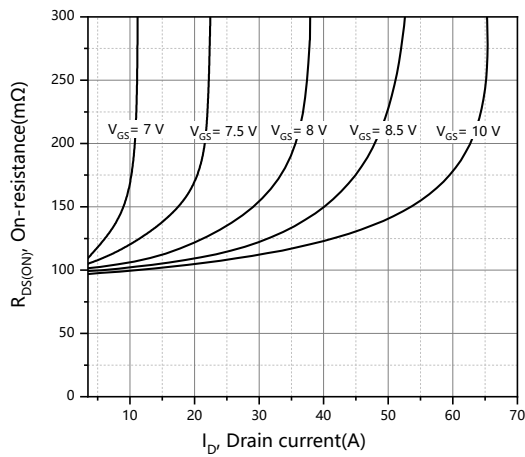
**Figure 6. Drain-source on-state resistance**



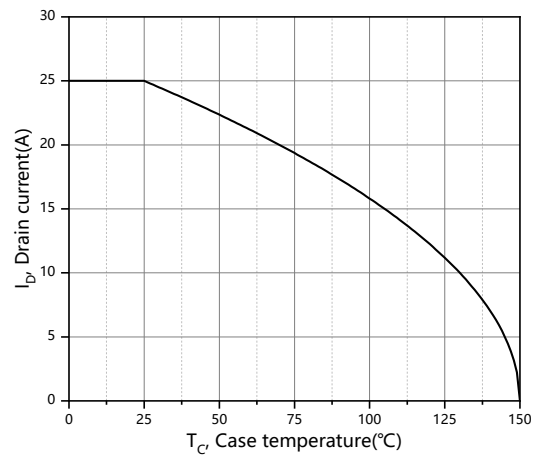
**Figure 7. Threshold voltage**



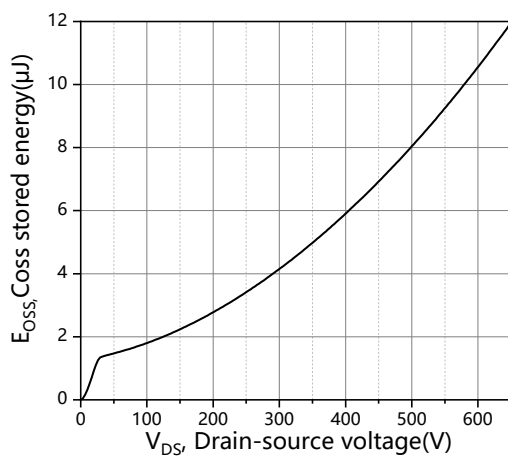
**Figure 8. Forward characteristic of body diode**



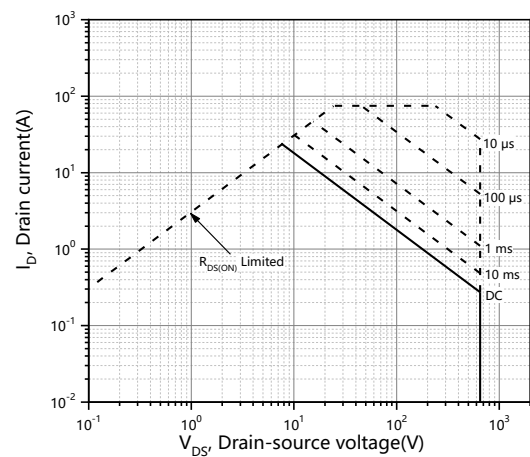
**Figure 9. Drain-source on-state resistance**



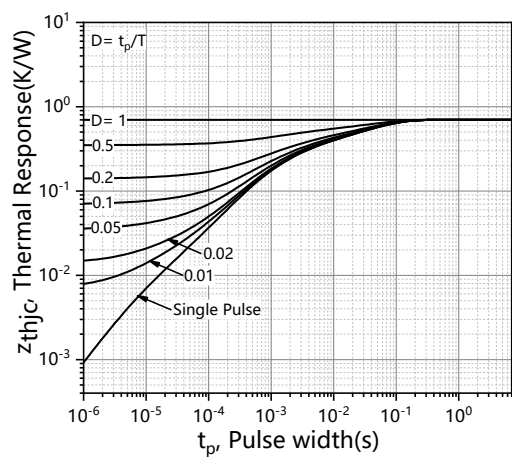
**Figure 10. Drain current**



**Figure 11. Typ. Coss stored energy**



**Figure 12. Safe operation area  $T_c=25^\circ\text{C}$**



**Figure 13. Max. transient thermal impedance**

## Test circuits and waveforms



**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveforms**

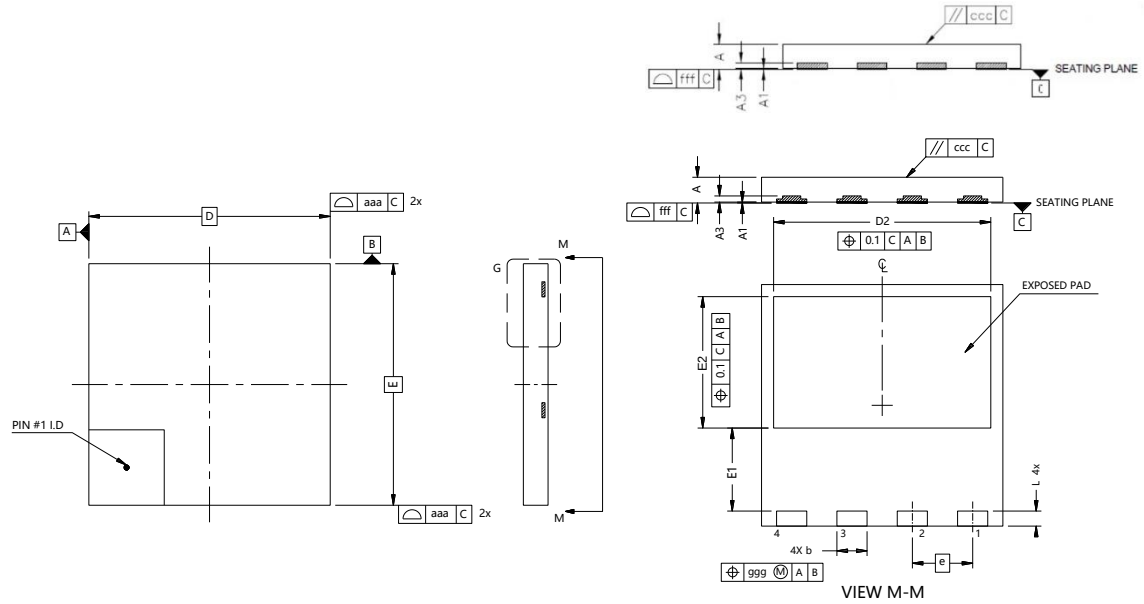


**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**



**Figure 4. Diode reverse recovery test circuit & waveforms**

## Package Information



| Symbol | mm      |      |
|--------|---------|------|
|        | Min     | Max  |
| A      | 0.75    | 0.95 |
| A1     | 0.00    | 0.05 |
| A3     | 0.10    | 0.30 |
| b      | 0.90    | 1.10 |
| D      | 7.90    | 8.10 |
| E      | 7.90    | 8.10 |
| D2     | 7.10    | 7.30 |
| E1     | 2.65    | 2.85 |
| E2     | 4.25    | 4.45 |
| e      | 2.0 BSC |      |
| L      | 0.40    | 0.60 |
| aaa    | 0.1     |      |
| ggg    | 0.05    |      |
| ccc    | 0.05    |      |
| fff    | 0.05    |      |

Version 1: PDFN8\*8-S package outline dimension

### Ordering Information

| Package Type | Units/ Reel | Reel s/ Inner Box | Units/ Inner Box | Inner Boxes/ Carton Box | Units/ Carton Box |
|--------------|-------------|-------------------|------------------|-------------------------|-------------------|
| PDFN8*8-S    | 3000        | 1                 | 3000             | 10                      | 30000             |

### Product Information

| Product          | Package | Pb Free | RoHS | Halogen Free |
|------------------|---------|---------|------|--------------|
| OSG65R130JT3ZF-F | PDFN8*8 | yes     | yes  | yes          |

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